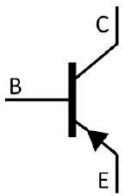


Silicon PNP transistor in a TO-252 Plastic Package.

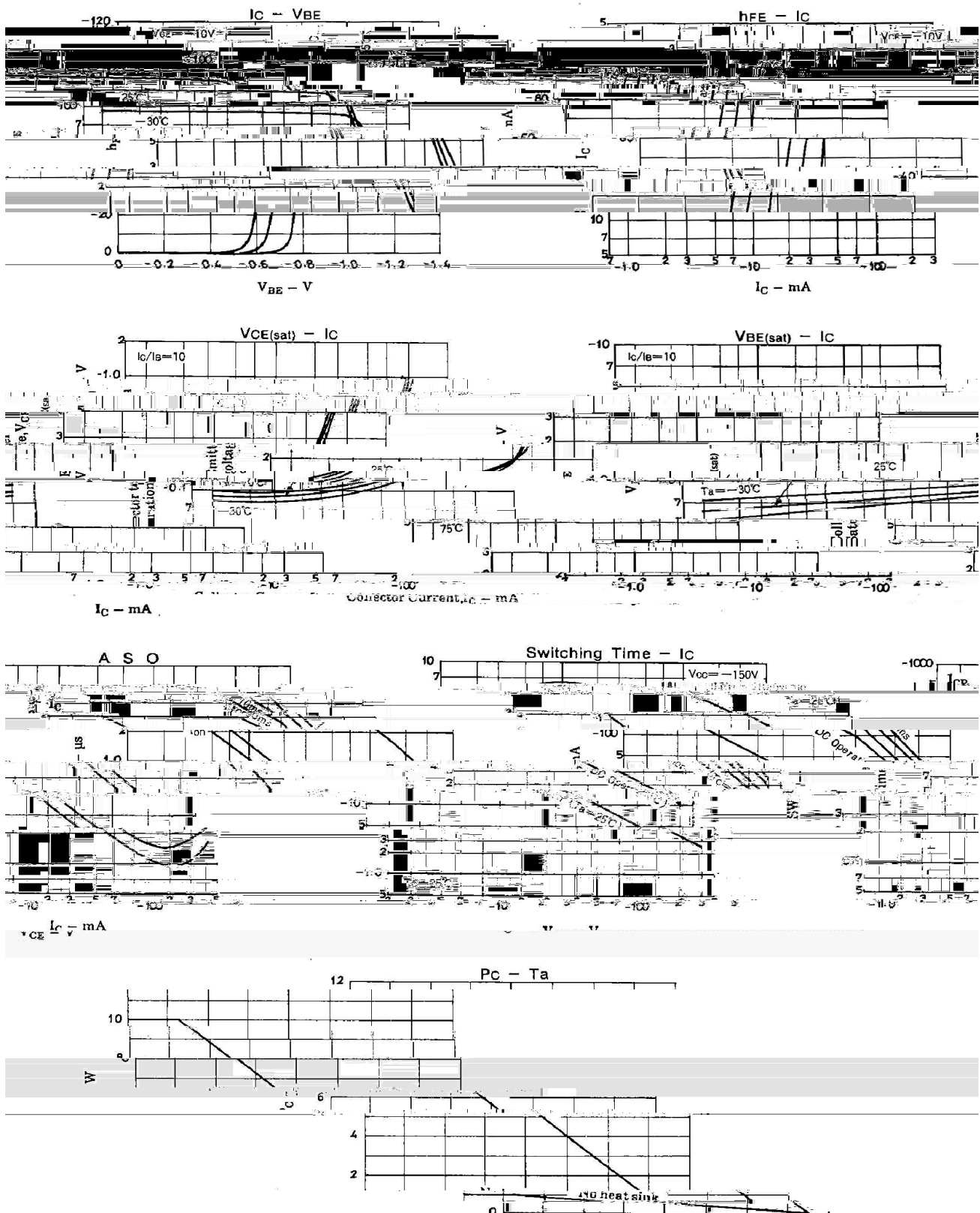
High breakdown voltage, adoption of MBIT process excellent h_{FE} linearity

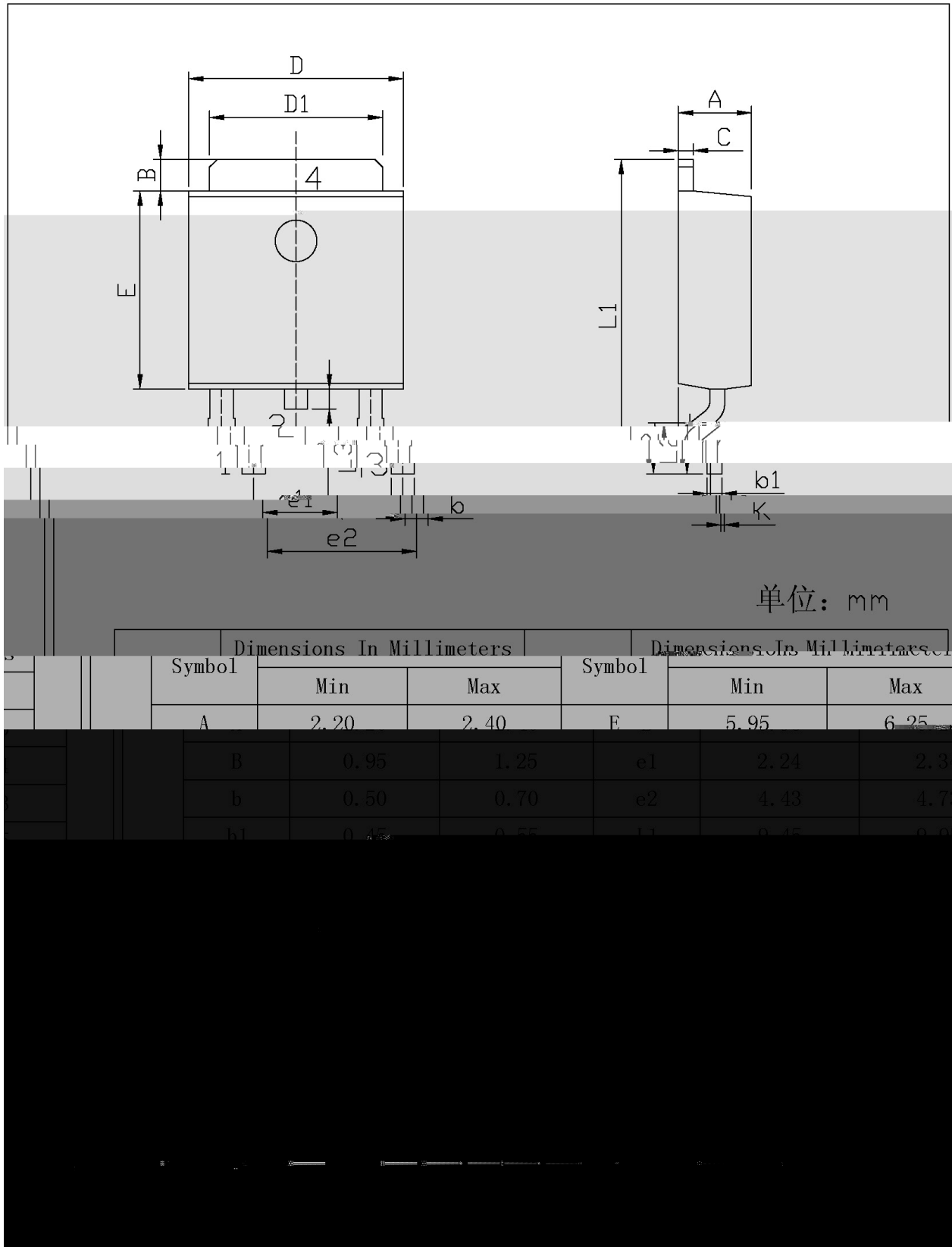
High voltage driver applications.

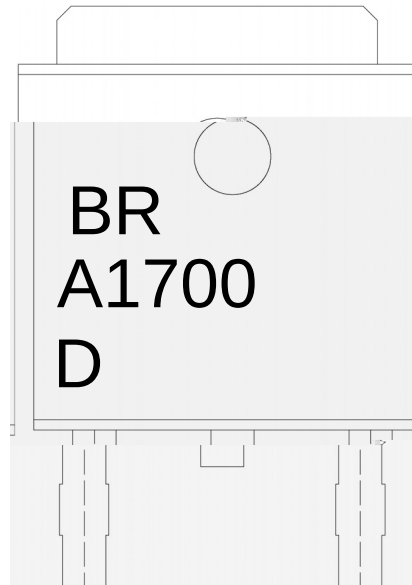


Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-400	V
Collector to Emitter Voltage	V_{CEO}	-400	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-200	mA
Collector Current – Continuous(Pulse)	I_{CP}	-400	mA
Collector Power Dissipation	P_C	1.0	W
Collector Power Dissipation	$P_C(T_c=25^\circ\text{C})$	10	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 ~ 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=-10\mu\text{A}$ $I_E=0$	-400			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-1.0\text{mA}$ $R_{BE}=\infty$	-400			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=-10\mu\text{A}$ $I_C=0$	-5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-300\text{V}$ $I_E=0$			-0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-4.0\text{V}$ $I_C=0$			-0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=-10\text{V}$ $I_C=-50\text{mA}$	60		200	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-50\text{mA}$ $I_B=-5.0\text{mA}$			-0.8	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-50\text{mA}$ $I_B=-5.0\text{mA}$			-1.0	V
Transition Frequency	f_T	$V_{CE}=-30\text{V}$ $I_C=-10\text{mA}$		70		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-30\text{V}$ $f=1.0\text{MHz}$		5.0		pF
Reverse Transfer Capacitance	C_{re}	$V_{CB}=-30\text{V}$ $f=1.0\text{MHz}$		4.0		pF
Turn-On Time	t_{on}	$10I_{B1}=-10I_{B2}=I_C=50\text{mA}$ $R_L=3K\Omega$ $R_B=200\Omega$ at $I_C=50\text{mA}$		0.25		μs
Turn-Off Time	t_{off}			5.0		μs







BR

A1700

D

h_{FE}

Note:

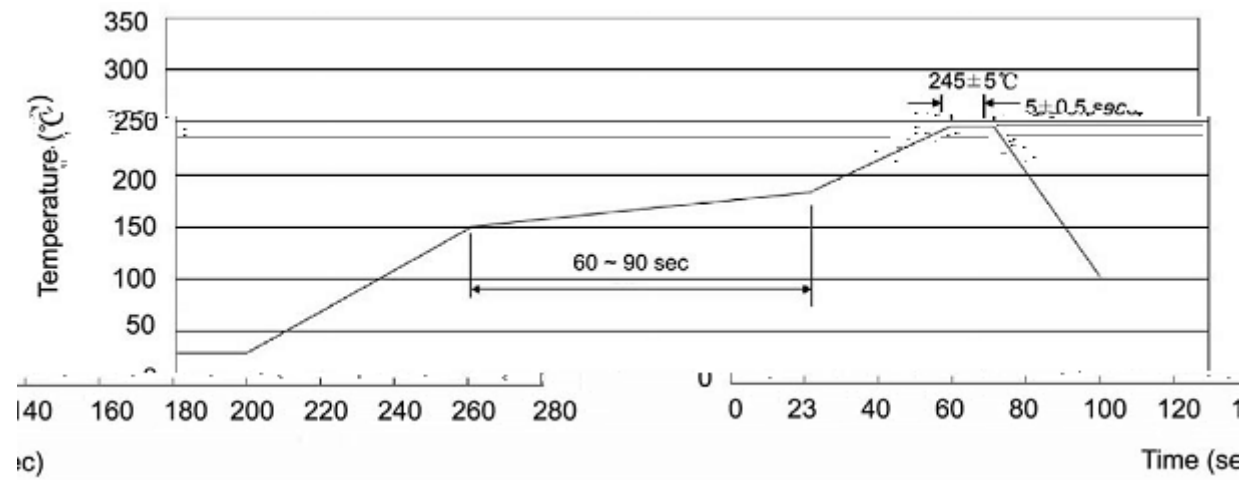
BR: Company Code

A1700: Product Type Code.

D: h_{FE} Classifications Symbol

****: Lot No. Code, code change with Lot No.

Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- 1

25 150

60 90sec;
- 2

245 5

5 0.5sec;
- 3

2 10 /sec.
- 1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:245 5 , Duration:5 0.5sec.

3. Cooling Speed: 2~10 /sec.

260 5 10 1 sec. Temp.:260±5 Time:10±1 sec

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 卷盘	卷盘 盒	只 盒	盒 箱	只 箱		盒	箱

/ TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 套管	套管 盒	只 盒	盒 箱	只 箱	套管	盒	箱